

Supporting Information

Cation disorder and thermoelectric properties in layered ternary compounds MBi_2Te_4 (M=Ge, Sn)

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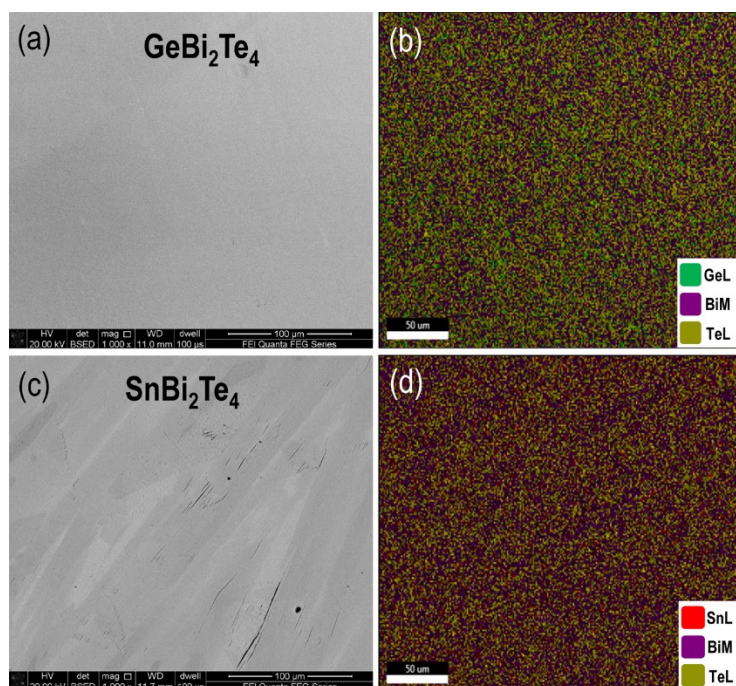


Fig. S1 Backscattered electron (BSE) images and elemental maps of GeBi_2Te_4 and SnBi_2Te_4 obtained in scanning electron microscope (SEM). The BSE-SEM images

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displayed in (a) and (c) show a morphology of GeBi_2Te_4 and SnBi_2Te_4 samples. The contrast appeared in (a) and (c) results from the grains of different orientations. The corresponding elemental maps of GeBi_2Te_4 and SnBi_2Te_4 samples presented in (b) and (d) indicate a homogeneous distribution of constituent elements (Ge, Sn, Bi, and Te) in the samples.

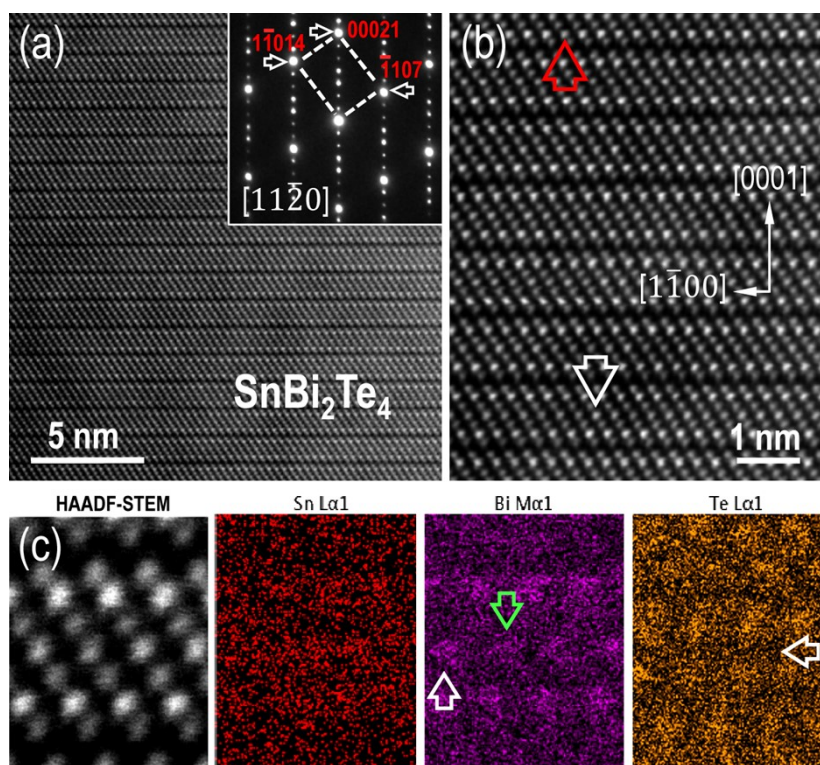


Fig. S2 The cation disorder in SnBi_2Te_4 . (a, b) HAADF-STEM images of SnBi_2Te_4 viewed along the $[11\bar{2}0]$ zone axis. The insert in (a) is the corresponding SAED pattern. In (b), the intensity variation in the $3a$ site occupied by Sn, and the $6c$ site occupied by Bi is demonstrated by a vertical white arrow and a vertical red arrow, respectively. (c) HAADF-STEM image and the atomically resolved EDS maps of Sn-L α 1, Bi-M α 1, and Te-L α 1 of the SnBi_2Te_4 sample viewed along the $[11\bar{2}0]$ zone axis. The intensity fluctuation can be visible in the $3a$ site, as displayed by a vertical white arrow and a vertical green arrow, indicating the substitution of Sn cations by Bi cations in different ratios. The atomic plane of the $3a$ site is marked by a horizontal white arrow.